







<https://doi.org/10.1038/s41467-021-23392-6>

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Author Correction: Van der Waals engineering of ferroelectric heterostructures for long-retention memory

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Correction to: *Nature Communications* <https://doi.org/10.1038/s41467-021-21320-2>, published online 17 February 2021.

The original version of this Article contained an error in the Acknowledgements:

NRF-CRP22-2019-0060 should have read NRF-CRP22-2019-0007.

This has now been corrected in both the PDF and HTML versions of the Article.

Published online: 10 May 2021



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